

Slew Rate Controlled Load Switch

FEATURES

- 1.8 V to 5.5 V Input Voltage range
- Very Low $R_{DS(ON)}$, typically 80 m Ω (5 V)
- Slew rate limited turn-on time options
 - SiP4280-1: 1 ms
 - SiP4280-3: 100 μ s
- Fast shutdown load discharge option
- Low quiescent current
- 4 kV ESD Rating
- 8 pin SC70JW package
- 6 pin SOT23 package

DESCRIPTION

The SiP4280 is a P-Channel MOSFET power switch designed for high-side load switching applications. The output pass transistor is a P-Channel MOSFET transistor with typically 80 m Ω $R_{DS(ON)}$. The SiP4280 is available in two different versions of turn-on times. The SiP4280-1 version has a slew rate limited turn-on time typically of 1 ms. The SiP4280-3 version has a slew rate limited turn-on time typically of 100 μ s and additionally offers a shutdown load discharge circuit to rapidly turn off a load circuit when the switch is disabled.

Both SiP4280 load switch versions operate with an

APPLICATIONS

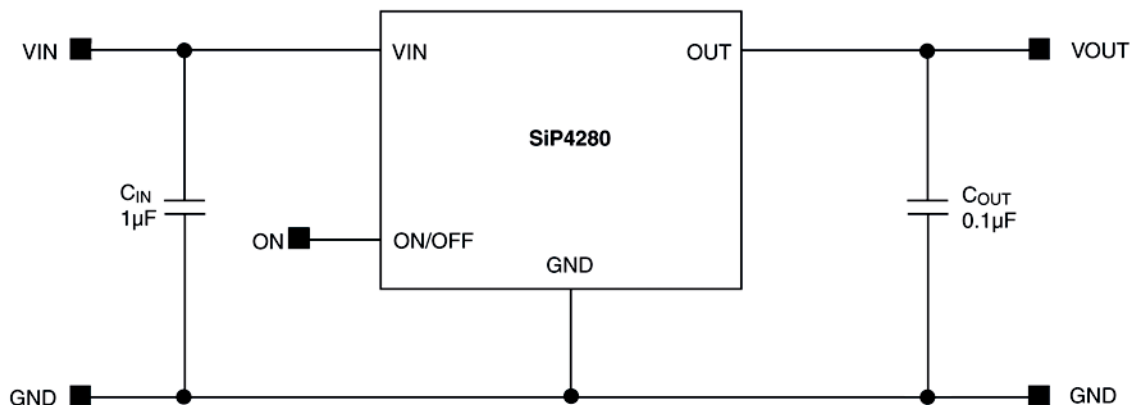
- Cellular telephones
- Digital still cameras
- Personal digital assistants (PDA)
- Hot swap supplies
- Notebook computers
- Personal communication devices



input voltage ranging from 1.8 V to 5.5 V, making them ideal for both 3 V and 5 V applications. The SiP4280 also features an under-voltage lock out which turns the switch off when an input undervoltage condition exists. Input logic levels are TTL and 2.5 V to 5.0 V CMOS compatible. The quiescent supply current is very low, typically 2.5 μ A. In shutdown mode, the supply current decreases to less than 1.0 μ A.

The SiP4280 is available in a 8 pin SC70JW or 6 pin SOT23 package and is specified over - 40 $^{\circ}$ C to 85 $^{\circ}$ C temperature range.

TYPICAL APPLICATION CIRCUIT



ABSOLUTE MAXIMUM RATINGS				
Parameter		Symbol	Steady State	Unit
Supply Input Voltage		V_{IN}	- 0.3 to 6	V
Enable Input Voltage		V_{ON}	- 0.3 to 6	
Output Voltage		V_{OUT}	- 0.3 to $V_{IN} + 0.3$	
Maximum Switch Current		I_{MAX}	2.3	A
Maximum Pulsed Current	$V_{IN} \geq 2.5$	I_{DM}	6	
	$V_{IN} < 2.5$	I_{DM}	3	
Junction Temperature		T_J	- 40 to 150	°C
Thermal Resistance	SC70JW-8L	Φ_{JA}^a	140	°C/W
	SOT23-6L		180	
Power Dissipation	SC70JW-8L ^b	P_D	714	mW
	SOT23-6L ^c	P_D	440	

Notes:

a. Device mounted with all leads soldered or welded to PC board.

b. Derate 7.14 mW/°C above $T_A = 25^\circ\text{C}$.c. Derate 5.5 mW/°C above $T_A = 70^\circ\text{C}$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE all voltages referenced to GND = 0 V				
Parameter		Symbol	Steady State	Unit
		V_{IN}	1.8 to 5.5	V
Operating Temperature Range			- 40 to 85	°C

SPECIFICATIONS						
Parameter	Symbol	Test Conditions Unless Specified $V_{IN} = 5\text{ V}, T_A = -40\text{ to }+85^\circ\text{C}$	Limits			Unit
			Min ^a	Typ ^b	Max ^a	
SiP4280 All Versions						
Operating Voltage ^c	V_{IN}		1.8	-	5.5	V
Undervoltage Lockout	V_{UVLO}	V_{IN} Falling	1.0	1.4	1.8	
Undervoltage Lockout Hysteresis	$V_{UVLO(hyh)}$		-	250	-	mV
Quiescent Current	I_Q	ON/OFF = active	-	2.5	4	μA
Off Supply Current	$I_{Q(OFF)}$	ON/OFF = inactive, OUT = open	-	0.01	1	
Off Switch Current	$I_{SD(OFF)}$	ON/OFF = inactive, $V_{OUT} = 0$	-	0.01	1	
On-Resistance	$R_{DS(ON)}$	$V_{IN} = 5\text{ V}, T_A = 25^\circ\text{C}$	-	80	120	m Ω
		$V_{IN} = 4.2\text{ V}, T_A = 25^\circ\text{C}$	-	85	130	
		$V_{IN} = 3\text{ V}, T_A = 25^\circ\text{C}$	-	100	150	
		$V_{IN} = 1.8\text{ V}, T_A = 25^\circ\text{C}$	-	160	250	
On-Resistance Temp-Coefficient	TC_{RDS}		-	2800	-	ppm/°C
ON/OFF Input Low Voltage ^d	V_{IL}	$V_{IN} = 2.7\text{ V to }5.5\text{ V}$	-	-	0.8	V
ON/OFF Input High Voltage	V_{IH}	$V_{IN} = 2.7\text{ V to } \leq 4.2\text{ V}$	2	-	-	
		$V_{IN} > 4.2\text{ V to }5.5\text{ V}$	2.4	-	-	
ON/OFF Input Leakage	I_{SINK}	$V_{ON/OFF} = 5.5\text{ V}$	-	-	1	μA
SiP4280-1 Version						
Output Turn-On Delay Time	$T_{D(ON)}$	$V_{IN} = 5\text{ V}, R_{LOAD} = 10\ \Omega, T_A = 25^\circ\text{C}$	-	20	40	μS
Output Turn-On Rise Time	T_{ON}	$V_{IN} = 5\text{ V}, R_{LOAD} = 10\ \Omega, T_A = 25^\circ\text{C}$	-	1000	1500	
Output Turn-Off Delay Time	$T_{D(OFF)}$	$V_{IN} = 5\text{ V}, R_{LOAD} = 10\ \Omega, T_A = 25^\circ\text{C}$	-	4	10	
SiP4280-3 Version						
Output Turn-On Delay Time	$T_{D(ON)}$	$V_{IN} = 5\text{ V}, R_{LOAD} = 10\ \Omega, T_A = 25^\circ\text{C}$	-	20	40	μS
Output Turn-On Rise Time	T_{ON}	$V_{IN} = 5\text{ V}, R_{LOAD} = 10\ \Omega, T_A = 25^\circ\text{C}$	-	100	150	
Output Turn-Off Delay Time	$T_{D(OFF)}$	$V_{IN} = 5\text{ V}, R_{LOAD} = 10\ \Omega, T_A = 25^\circ\text{C}$	-	4	10	
Output Pull-Down Resistance	R_{PD}	ON/OFF = inactive, $T_A = 25^\circ\text{C}$	-	150	250	Ω

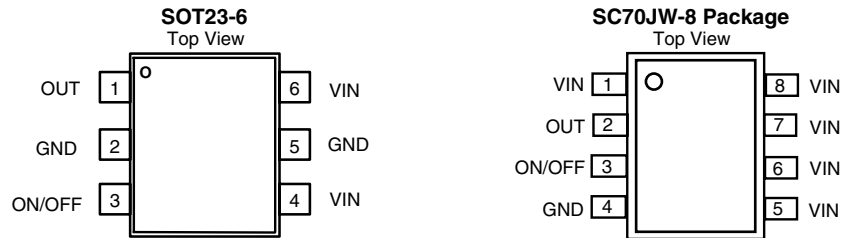
Notes:

a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum.

b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

c. Part requires minimum start-up of $V_{IN} \geq 2.0$ to ensure operation down to 1.8 V.d. For $V_{IN} \leq 2.7\text{ V}$ see typical ON/OFF threshold curve.

PIN CONFIGURATION

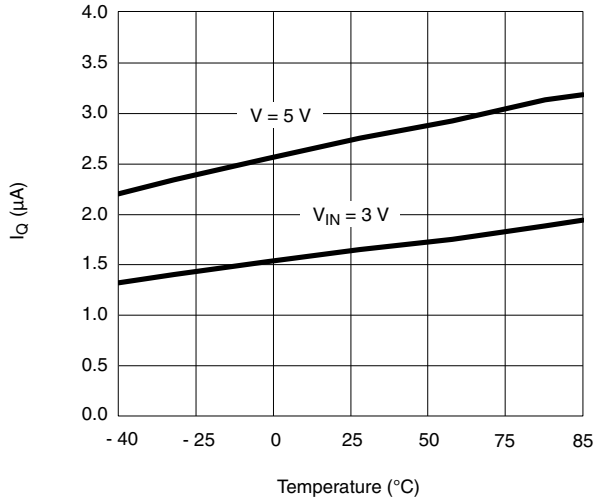


PIN DESCRIPTION			
Pin Number SC70JW-8	Pin Number SOT23-6	Pin Name	Symbol
1, 5, 6, 7, 8	4, 6	VIN	This pin is the P-channel MOSFET source connection
3	3	ON/OFF	Logic high enables the IC; logic low disables the IC and reduces the IC and reduces the quiescent current to 2.5 μ A
4	2, 5	GND	Ground connection
2	1	OUT	This pin is the P-channel MOSFET drain connection

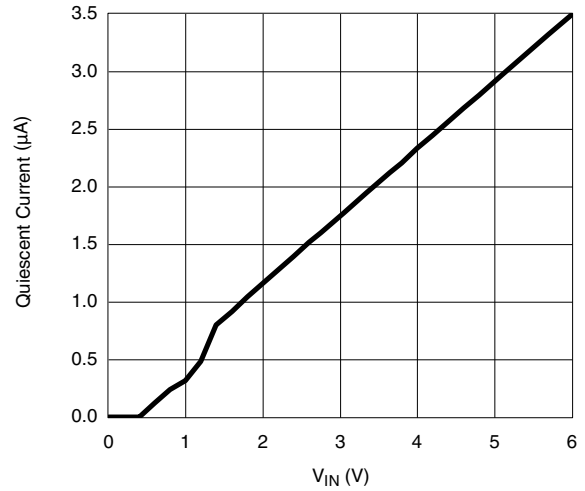
SELECTION GUIDE			
Part Number	Slew Rate (typ)	Active Pull Down	Enable
SiP4280-1-T1-E3	1 ms	No	Active High
SiP4280-3-T1-E3	100 μ s	Yes	Active High

ORDERING INFORMATION			
Part Number	Marking	Temperature Range	Package
SiP4280DR-1-T1-E3	L1XXX	- 40 °C to 85 °C	SC70JW-8L
SiP4280DR-3-T1-E3	L3XXX		SC70JW-8L
SiP4280DT-1-T1-E3	L1XXX		SOT23-6L
SiP4280DT-3-T1-E3	L3XXX		SOT23-6L

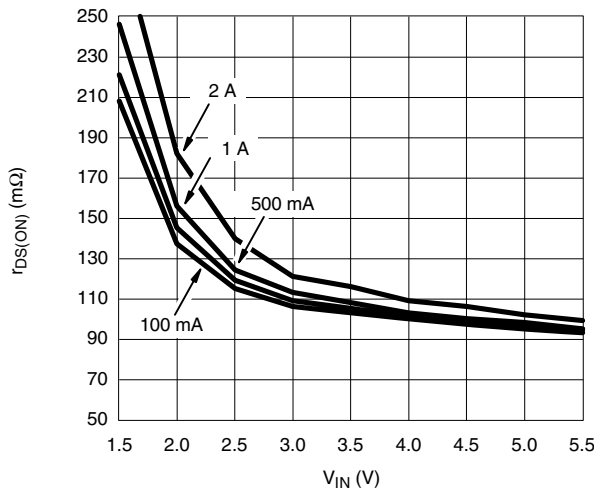
TYPICAL CHARACTERISTICS internally regulated, 25 °C unless noted



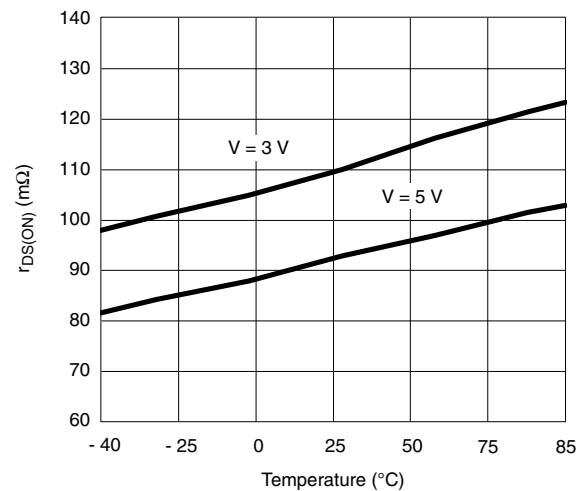
Quiescent Current vs. Temperature



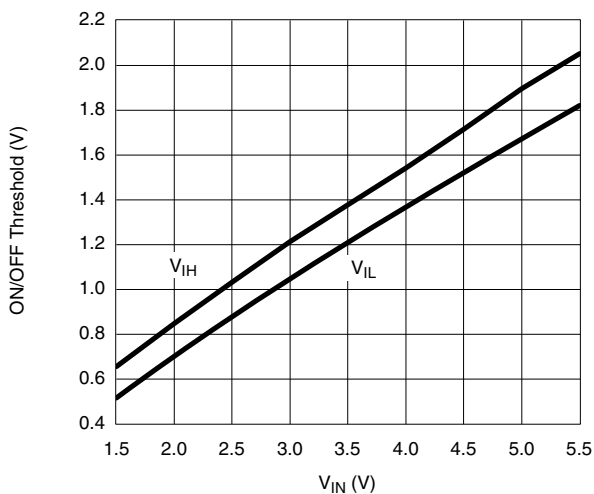
Quiescent Current vs. Input Voltage



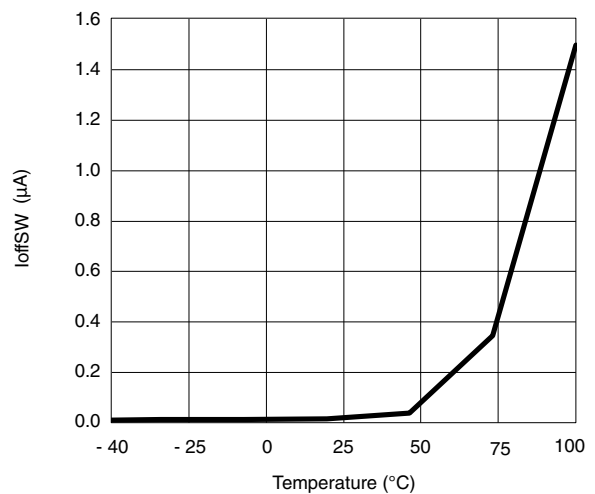
$R_{DS(ON)}$ vs. Input Voltage



$R_{DS(ON)}$ vs. Temperature

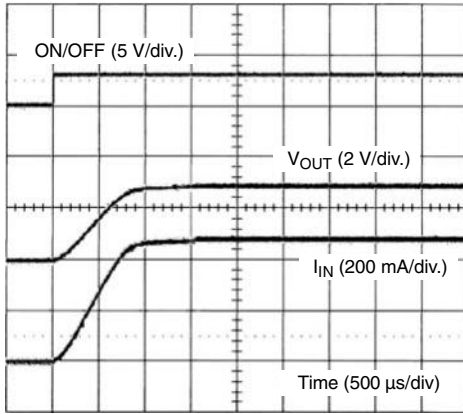


ON/OFF Threshold vs. Input Voltage

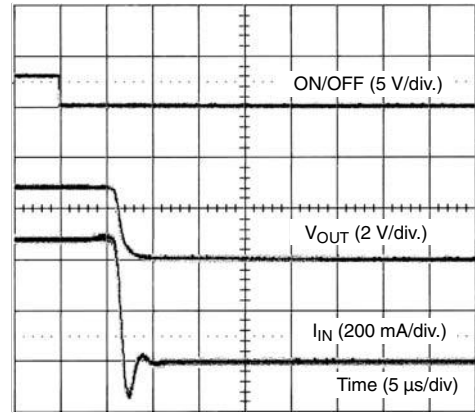


Off Switch Current vs. Temperature

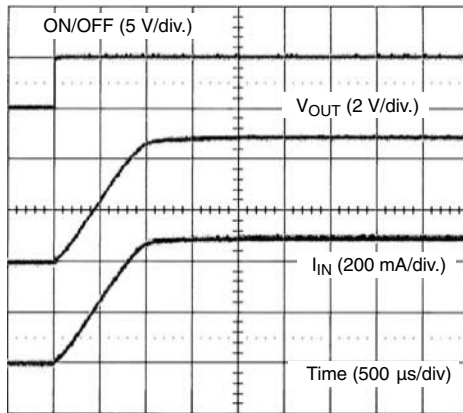
TYPICAL WAVEFORMS



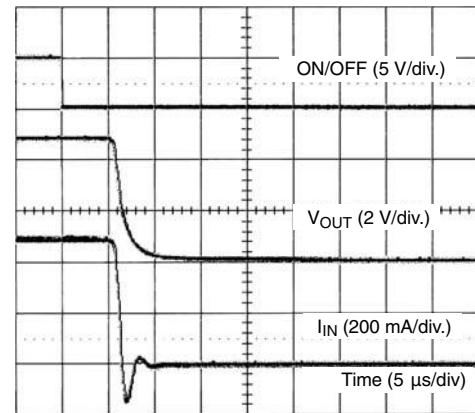
SiP4280-1 Turn-On ($V_{IN} = 3\text{ V}$, $R_{LOAD} = 6\ \Omega$)



SiP4280-1 Turn-Off ($V_{IN} = 3\text{ V}$, $R_{LOAD} = 6\ \Omega$)

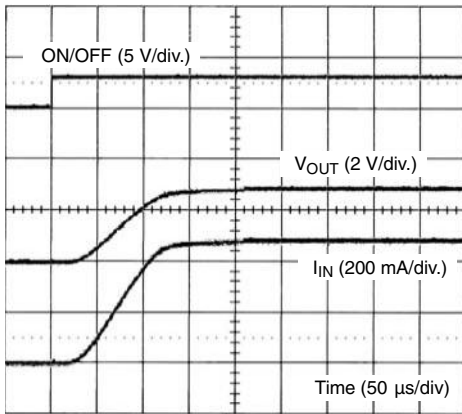


SiP4280-1 Turn-On ($V_{IN} = 5\text{ V}$, $R_{LOAD} = 10\ \Omega$)

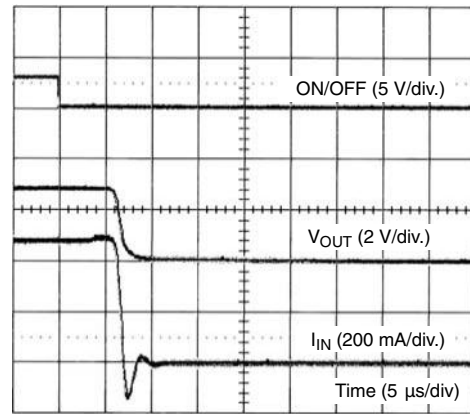


SiP4280-1 Turn-Off ($V_{IN} = 5\text{ V}$, $R_{LOAD} = 10\ \Omega$)

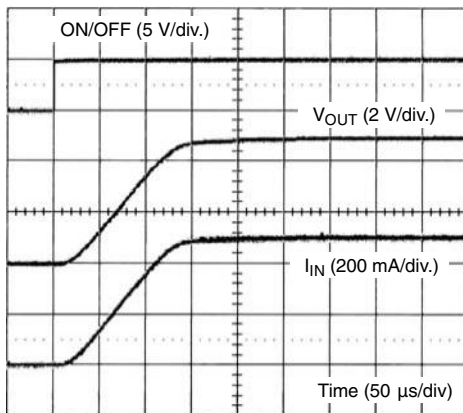
TYPICAL WAVEFORMS



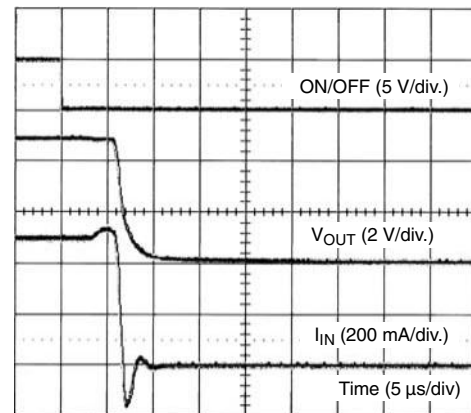
SiP4280-3 Turn-On ($V_{IN} = 3$ V, $R_{LOAD} = 6$ Ω)



SiP4280-3 Turn-Off ($V_{IN} = 3$ V, $R_{LOAD} = 6$ Ω)

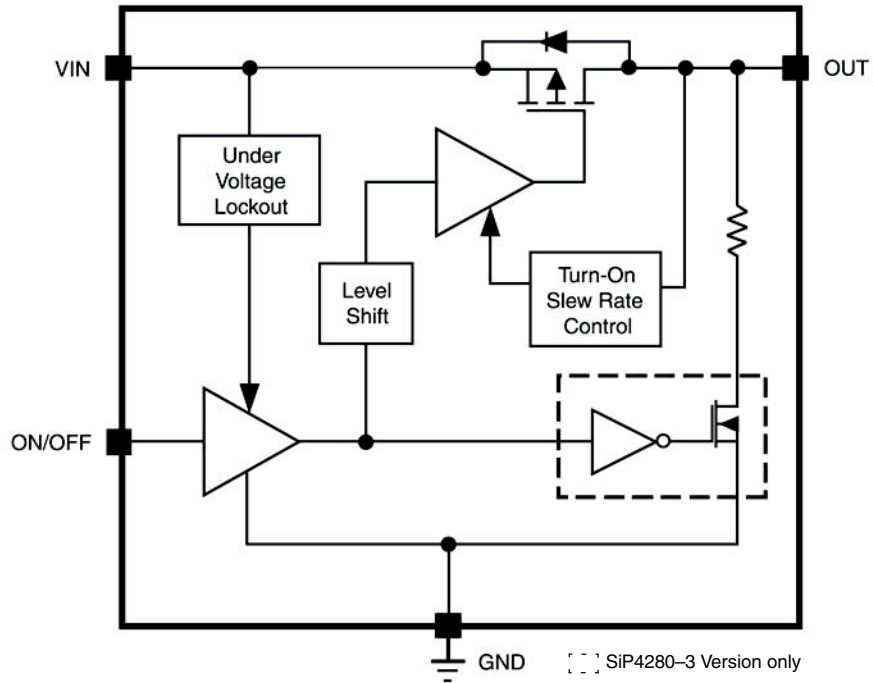


SiP4280-3 Turn-On ($V_{IN} = 5$ V, $R_{LOAD} = 10$ Ω)



SiP4280-3 Turn-Off ($V_{IN} = 5$ V, $R_{LOAD} = 10$ Ω)

BLOCK DIAGRAM



SiP4280 Functional Block Diagramm

DETAILED DESCRIPTION

The SiP4280 is a P-Channel MOSFET power switches designed for high-side slew rate controlled load-switching applications. During turn on, the current ramps linearly until it reaches the level required for the output load condition. This is achieved by first applying the threshold voltage on the gate of the MOSFET. Once at this level, the current begins to slew and the gate voltage is then linearly increased until the MOSFET becomes fully enhanced. Once fully enhanced, the gate is quickly increased to the full input voltage and $R_{DS(ON)}$ is minimized.

The SiP4280-1 version has a moderate 1ms turn on slew rate feature, which reduces in-rush current when the MOSFET is turned on. This function allows the load switch to be implemented with a small input capacitor, or no input capacitor at all. The SiP4280-3 has in addition to the 100 μ s minimized slew rate limited turn on

function, a shutdown output discharge circuit to rapidly turn off a load when the load switch is disabled through the ON/OFF pin.

Both versions of the SiP4280 operate with input voltages ranging from 1.8 V to 5.5 V. Also, both versions of this device have extremely low operating current, making them ideal for battery-powered applications. In cases where the input voltage drops below 1.8 V, the under voltage lockout function will prevent the P-Channel MOSFET device from entering into the saturation region of operation by automatically shutting down SiP4280. The ON/OFF control pin is TTL compatible and will also function with 2.5 V to 5 V CMOS logic systems.

APPLICATION INFORMATION

Input Capacitor

While a bypass capacitor on the input is not required, a 1 μ F or larger capacitor for C_{IN} is recommended in almost all applications. The Bypass capacitor should be placed as physically close as possible to the SiP4280 to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

Output Capacitor

A 0.1 μ F capacitor or larger across V_{OUT} and GND is recommended to insure proper slew operation. C_{OUT} may be increased without limit to accommodate any load transient condition with only minimal affect on the SiP4280 turn on slew rate time. There are no ESR or capacitor type requirement.

Enable

The ON/OFF pin is compatible with both TTL and CMOS logic voltage levels.

Reverse Voltage Conditions and Protection

The P-Channel MOSFET pass transistor has an intrinsic diode that is reversed biased when the input voltage is greater than the output voltage. Should V_{OUT} exceed V_{IN} , this intrinsic diode will become forward biased and allow excessive current to flow into the IC thru the V_{OUT} pin and potentially damage the IC device. Therefore extreme care should be taken to prevent V_{OUT} from exceeding V_{IN} .

In conditions where V_{OUT} exceeds V_{IN} a Schottky diode in parallel with the internal intrinsic diode is recommended to protect the SiP4280.



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